

09/295607

Sheet 1 of 2

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney D ck t No. 0756-1961

Serial No. N t Y t Assign d

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI t al.

Filing Date:

Group: 2812

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appr priate)
Loke	4,727,044	2/23/88	Yamazaki			
Loke	4,959,700	9/25/90	Yamazaki			
Loke	5,142,344 8-25-1992	5/24/91	Yamazaki			
Loke	4,415,383	11/15/83	Naem et al.			
Loke	4,523,962	6/18/85	Nishimura			
Loke	4,431,459	2/14/84	Teng			
Loke	4,851,363	7/25/89	Troxel et al.			
Loke	4,959,700	9/25/90	Yamazaki			2/3/88
Loke	5,306,651	4/26/94	Masumo et al.	437	40	5/10/91
Loke	4,561,906	12/31/85	Calder et al.	437	101	10/24/83
Loke	5,091,334	2/25/92	Yamazaki et al.	437	101	6/29/81
Loke	5,272,361	12/21/93	Yamazaki	257	66	6/13/90

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	Document Number	Date	Country	Class	Subclass	Translation Yes No
Loke	59-121876	7/14/84	Japan			Abstract
Loke	60-245174	12/4/85	Japan			Abstract
Loke	6-59280	3/4/94	Japan			Abstract
Loke	5-206468	8/13/93	Japan			Abstract
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Loke	Sameshima et al., Japanese Journal of Applied Physics, "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Vol. 28, No. 10, October, 1989, p. 1789-1793.
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*EXAMINER: Initial if citation consid red, wh ther or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not consid red. Includ copy of this form with n xt communicati n to applicant.

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Attorney Docket No. 0756-1961

Serial No. 09/295,607

Applicant: Shunpei YAMAZAKI et al.

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Filing Date: April 22, 1999

Group: 2811

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
Loke	5,147,826	09/15/92	Liu et al			
	5,275,851	01/04/94	Fonash et al			
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Loke	EP 0 474 289 A1	03/11/92	Europe			
	63-258063	10/25/88	Japan			Abstract
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	Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon", Appl. Phys. Lett., Vol. 60, No. 2, January 13, 1992, pp. 225-227
	Dvurenchenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", Phys. Stat. Sol. Vol. (a) 95, (1986), pp. 635-640
	Crowder et al., "DMOS FET with Common Field and Channel Doping", IBM Technical Disclosure Bulletin, Vol. 20, No. 4, September 1977, pp. 1617-1621
	Fathimulla et al., "Reactively rf Magnetron Sputtered AlN Films as Gate Dielectric", J. Appl. Phys., Vol. 54, No. 8, August 1983, pp. 4586-4589
Loke	Gerova, "Deposition of AlN Thin Films by Magnetron Reactive Sputtering", Thin Solid Films - Preparation and Characterization, Vol. 81, (1981), pp. 201-205

Examiner

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Date Considered

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Submitted with IDS of September 5, 2000

Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Atty Docket 0756-1961		Serial No. 09/295,607	
<div style="display: flex; align-items: center; justify-content: center;"> <div style="border: 1px solid black; border-radius: 50%; padding: 10px; text-align: center; margin-right: 10px;"> OIP MAY 16 2002 PATENT & TRADEMARK OFFICE </div> <div> INFORMATION DISCLOSURE STATEMENT </div> </div>				Applicants: Shunpei YAMAZAKI et al.			
				Filing Date: April 22, 1999		Group Art Unit: 2811	
U.S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)	
<div style="display: flex; align-items: center;"> <div style="writing-mode: vertical-rl; transform: rotate(180deg);"> AE 4-20 09 </div> <div style="margin-left: 10px;"> Loke ↓ Loke </div> </div>	2001/0050664	12/13/2001	Yamazaki et al.				
	4,468,855	09/04/1984	Sasaki				
	4,651,182	03/17/1987	Yamazaki				
	4,762,807	08/09/1988	Yamazaki				
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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No	
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	0 486 284	05/20/1992	EP			Full Eng	
	02-153896	06/13/1990	JP			Eng Abst	
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Examiner <u>Loke</u>			Date Considered <u>7/27/02</u>				
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